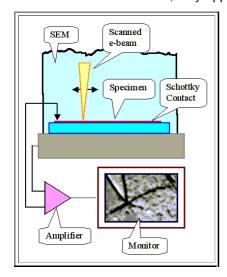
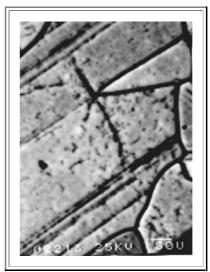
Principle of Electron Beam Induced Current Microscopy

- The "Electron Beam Induced Current method (EBIC) employs a (SEM) on a sample with a thin electron-transparent Schottky contact (usually evaporated AI). The Schottky contact is biased in reverse, the leakage current is amplified and displayed on a monitor synchronized with the electron beam scan.
 - The elecon beam induces carriers; the minority carriers either recombine at defects or are collected at the Schottky contact as current with the resulting signal being displayed on the monitor.
 - The picture on the monitor thus shows the efffective minority carrier life time. Defects that are "electronically active" reduce the currents; they appear in dark contrasts.



Principle of EBIC



Typical **EBIC** picture, showing electronically active defects in solar-grade **Si**.